



**THE DATASHEET OF
NTH4L014N120M3P**



Silicon Carbide (SiC) MOSFET – EliteSiC, 14 mohm, 1200 V, M3P, TO-247-4L

NTH4L014N120M3P

Features

- Typ. $R_{DS(on)}$ = 14 m Ω @ V_{GS} = 18 V
- Low Switching Losses (Typ. EON 1308 μ J at 74 A, 800 V)
- 100% Avalanche Tested
- These Devices are RoHS Compliant

Typical Applications

- Solar Inverters
- Electric Vehicle Charging Stations
- UPS (Uninterruptible Power Supplies)
- Energy Storage Systems
- SMPS (Switch Mode Power Supplies)

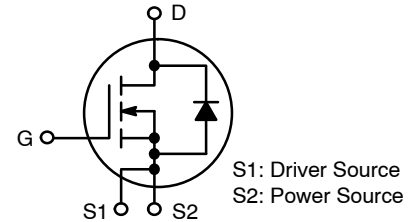
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	1200	V	
Gate-to-Source Voltage		V_{GS}	-10/+22	V	
Recommended Operation Values of Gate-to-Source Voltage		$T_C < 175^\circ\text{C}$ V_{GSop}	-5/+18	V	
Continuous Drain Current (Notes 1, 2)	Steady State	$T_C = 25^\circ\text{C}$	I_D	152	A
			P_D	686	W
Power Dissipation (Note 1)	Steady State	$T_C = 100^\circ\text{C}$	I_D	107	A
			P_D	343	W
Pulsed Drain Current (Note 2)		$T_C = 25^\circ\text{C}$	I_{DM}	407	A
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode) $T_C = 25^\circ\text{C}, V_{GS} = -3\text{ V}$		I_S	129	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 28.9\text{ A}, L = 1\text{ mH}$) (Note 4)		E_{AS}	418	mJ	
Maximum Lead Temperature for Soldering (1/25" from case for 10 s)		T_L	270	$^\circ\text{C}$	

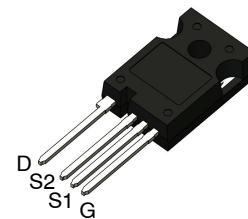
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The maximum current rating is based on typical $R_{DS(on)}$ performance.
3. Repetitive rating, limited by max junction temperature.
4. EAS of 418 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 1\text{ mH}$, $I_{AS} = 28.9\text{ A}$, $V_{DD} = 100\text{ V}$, $V_{GS} = 18\text{ V}$.

$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
1200 V	20 m Ω @ 18 V	152 A

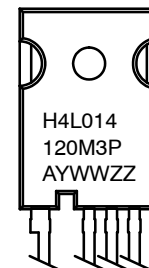


N-CHANNEL MOSFET



TO-247-4L
CASE 340CJ

MARKING DIAGRAM



H4L014120M3P = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping
NTH4L014N120M3P	TO-247-4L	30 Units / Tube

NTH4L014N120M3P

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Max	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	0.17	0.22	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$		40	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF-STATE CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1200	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1\text{ mA}$, referenced to 25°C (Note 6)	-	0.3	-	V/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 1200\text{ V}, T_J = 25^\circ\text{C}$	-	-	100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = +22/-10\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 1	μA

ON-STATE CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 37\text{ mA}$	2.08	3.0	4.63	V
Recommended Gate Voltage	V_{GOP}		-5	-	+18	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 18\text{ V}, I_D = 74\text{ A}, T_J = 25^\circ\text{C}$	-	14	20	m Ω
		$V_{GS} = 18\text{ V}, I_D = 74\text{ A}, T_J = 175^\circ\text{C}$ (Note 6)	-	29	-	
		$V_{GS} = 15\text{ V}, I_D = 74\text{ A}, T_J = 25^\circ\text{C}$	-	16	27	
		$V_{GS} = 15\text{ V}, I_D = 74\text{ A}, T_J = 150^\circ\text{C}$ (Note 6)	-	27	-	
Forward Transconductance	g_{FS}	$V_{DS} = 10\text{ V}, I_D = 74\text{ A}$ (Note 6)	-	29	-	S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 800\text{ V}$ (Note 6)	-	6230	-	pF
Output Capacitance	C_{OSS}		-	262	-	
Reverse Transfer Capacitance	C_{RSS}		-	29	-	
Total Gate Charge	$Q_G(TOT)$	$V_{GS} = -3/18\text{ V}, V_{DS} = 800\text{ V}, I_D = 74\text{ A}$ (Note 6)	-	322	-	nC
Threshold Gate Charge	$Q_G(TH)$		-	45	-	
Gate-to-Source Charge	Q_{GS}		-	51	-	
Gate-to-Drain Charge	Q_{GD}		-	81	-	
Gate-Resistance	R_G	$f = 1\text{ MHz}$	-	1.4	-	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -3/18\text{ V}, V_{DS} = 800\text{ V}, I_D = 74\text{ A}, R_G = 2\text{ }\Omega$ inductive load (Notes 5, 6)	-	26	-	ns
Rise Time	t_r		-	40	-	
Turn-Off Delay Time	$t_{d(OFF)}$		-	68	-	
Fall Time	t_f		-	13	-	μJ
Turn-On Switching Loss	E_{ON}		-	1308	-	
Turn-Off Switching Loss	E_{OFF}		-	601	-	
Total Switching Loss	E_{tot}		-	1909	-	

SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Source-Drain Diode Forward Current (Note 1)	I_{SD}	$V_{GS} = -3\text{ V}, T_C = 25^\circ\text{C}$ (Note 6)	-	-	127	A
Pulsed Source-Drain Diode Forward Current (Note 2)	I_{SDM}		-	-	407	

NTH4L014N120M3P

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SOURCE-DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	$V_{GS} = -3\text{ V}, I_{SD} = 74\text{ A}, T_J = 25^\circ\text{C}$	-	5.2	-	V
Reverse Recovery Time	t_{RR}	$V_{GS} = -3/18\text{ V}, I_{SD} = 74\text{ A},$ $dI_S/dt = 1000\text{ A}/\mu\text{s}, V_{DS} = 800\text{ V}$ (Note 6)	-	36	-	ns
Reverse Recovery Charge	Q_{RR}		-	332	-	nC
Reverse Recovery Energy	E_{REC}		-	14	-	μJ
Peak Reverse Recovery Current	I_{RRM}		-	19	-	A
Charge time	T_A		-	20	-	ns
Discharge time	T_B		-	16	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. E_{ON}/E_{OFF} result is with body diode

6. Defined by design, not subject to production test.

NTH4L014N120M3P

TYPICAL CHARACTERISTICS

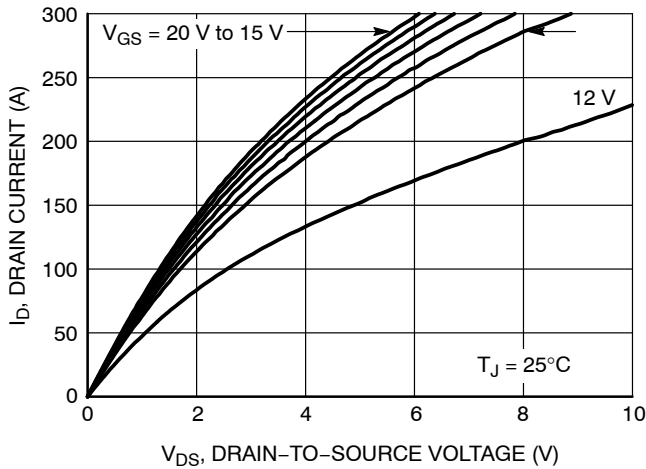


Figure 1. On-Region Characteristics

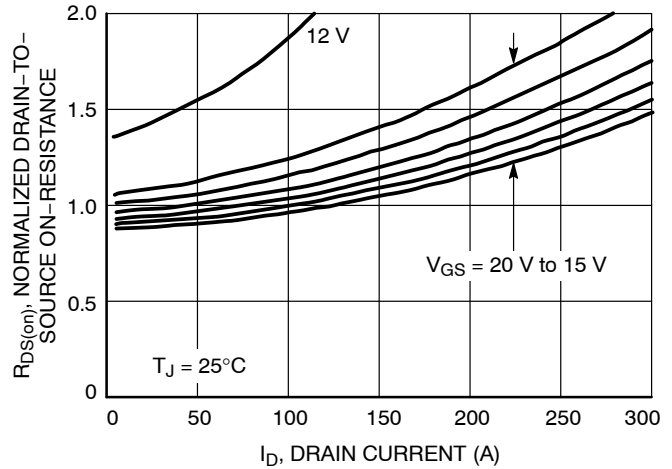


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

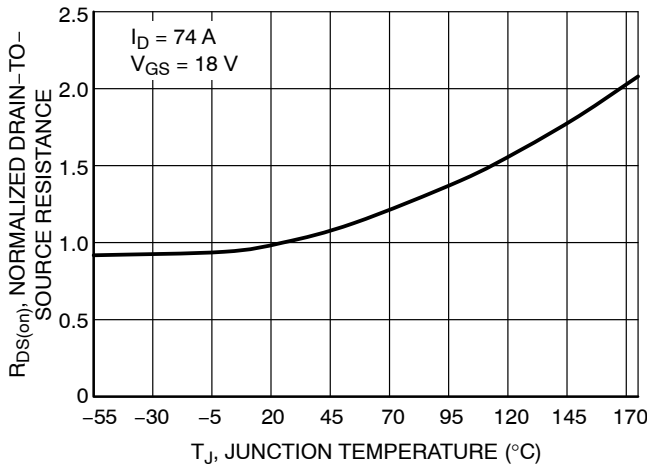


Figure 3. On-Resistance Variation with Temperature

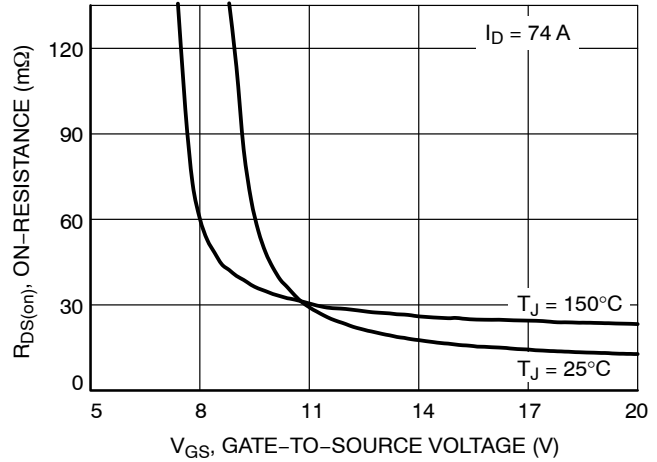


Figure 4. On-Resistance vs. Gate-to-Source Voltage

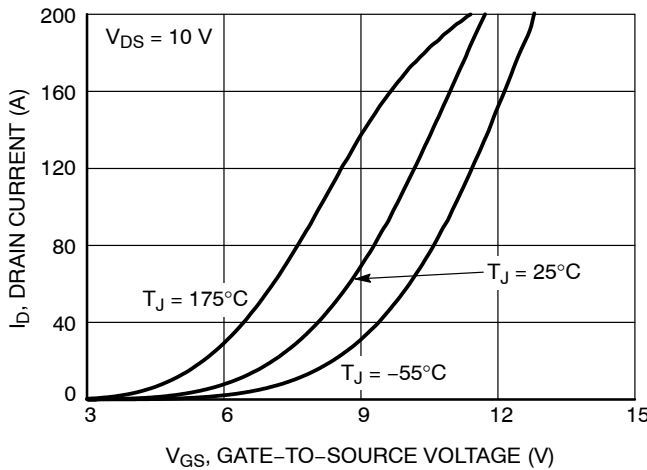


Figure 5. Transfer Characteristics

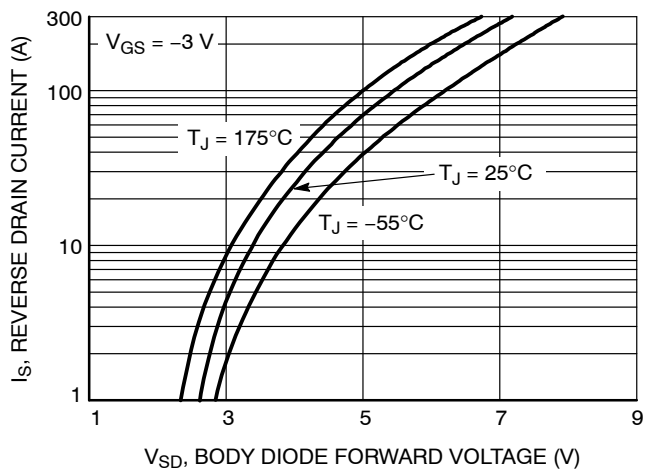


Figure 6. Diode Forward Voltage vs. Current

NTH4L014N120M3P

TYPICAL CHARACTERISTICS

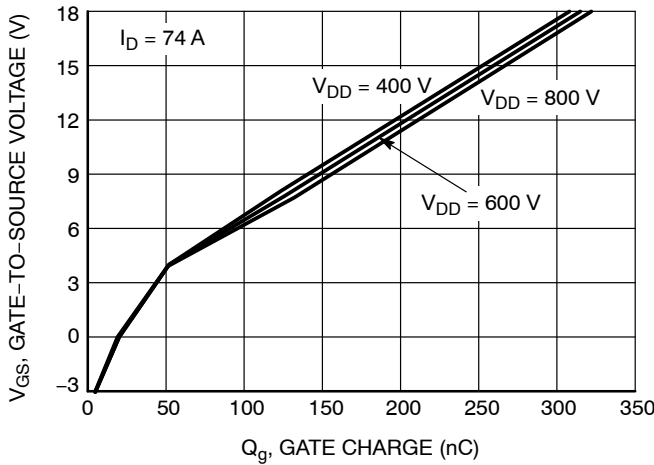


Figure 7. Gate-to-Source Voltage vs. Total Charge

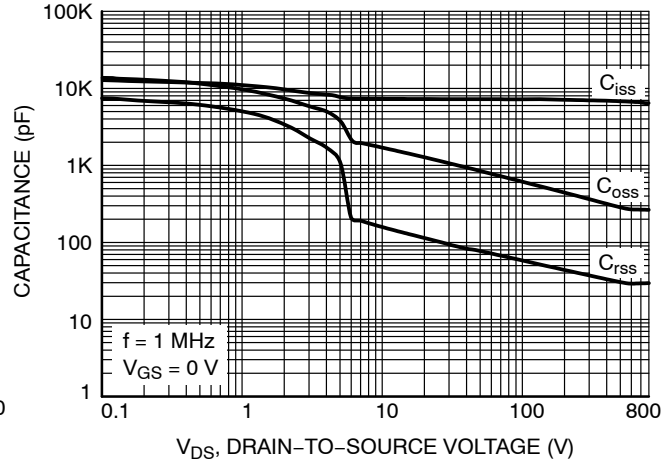


Figure 8. Capacitance vs. Drain-to-Source Voltage

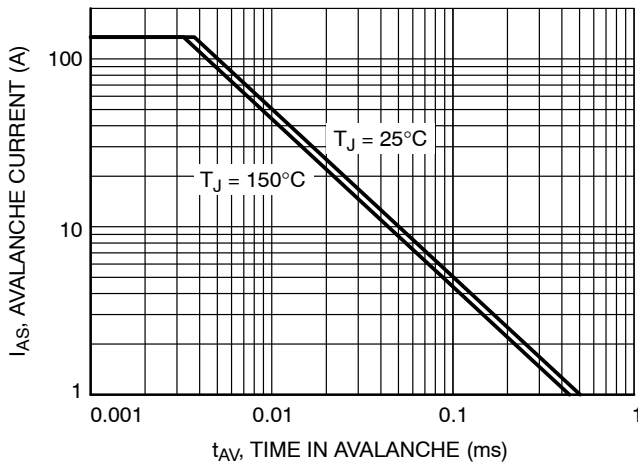


Figure 9. Unclamped Inductive Switching Capability

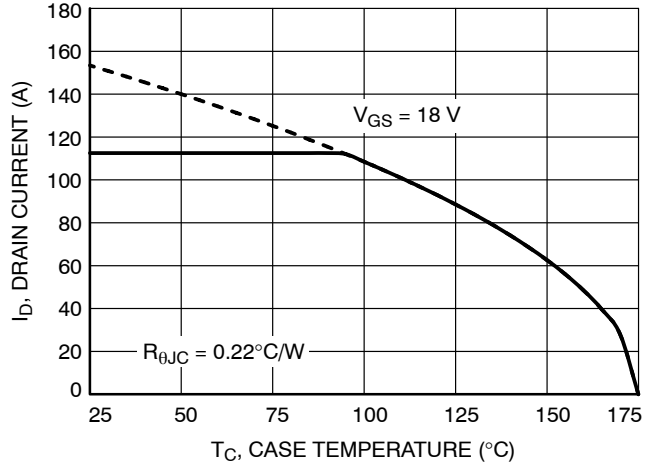


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

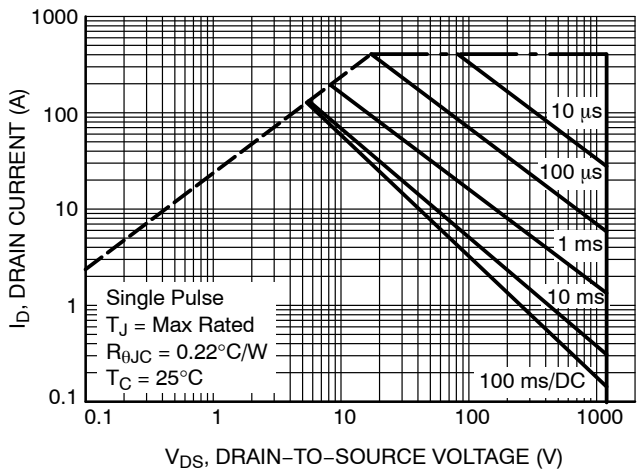


Figure 11. Safe Operating Area

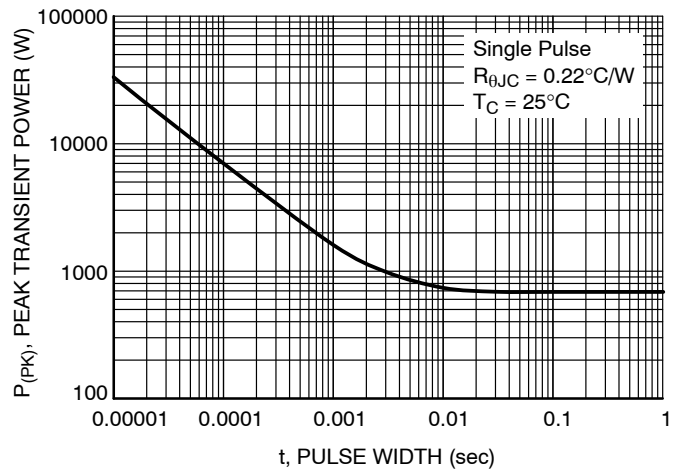


Figure 12. Single Pulse Maximum Power Dissipation

NTH4L014N120M3P

TYPICAL CHARACTERISTICS

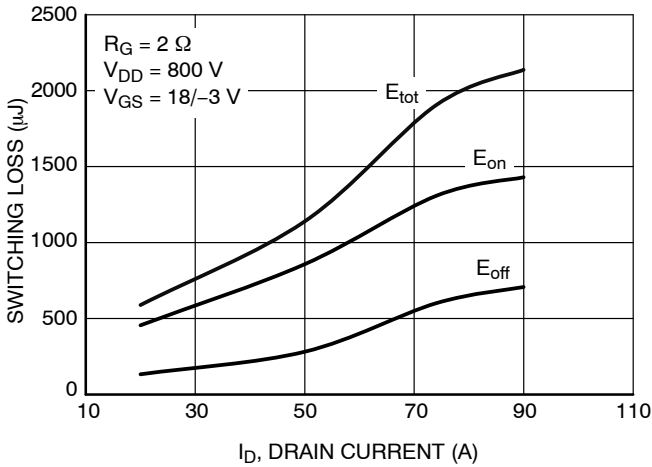


Figure 13. Switching Loss vs. Drain Current

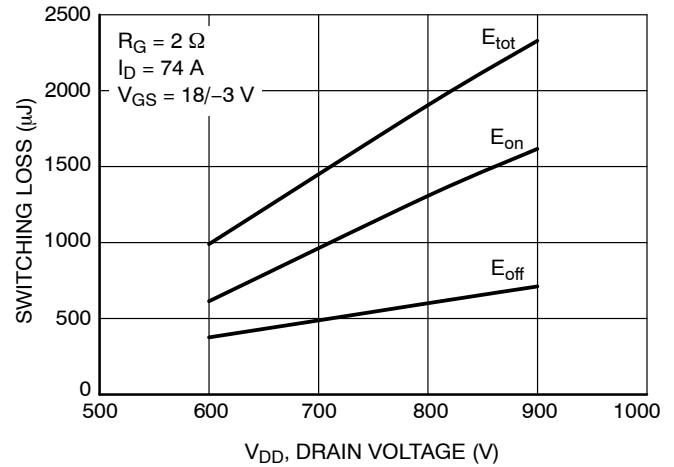


Figure 14. Switching Loss vs. Drain Voltage

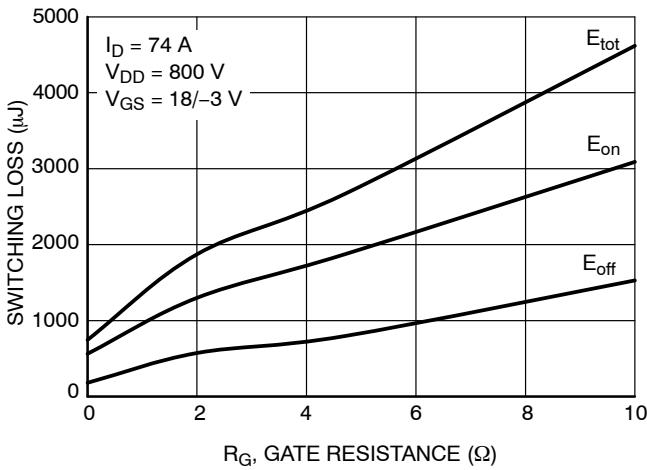


Figure 15. Switching Loss vs. Gate Resistance

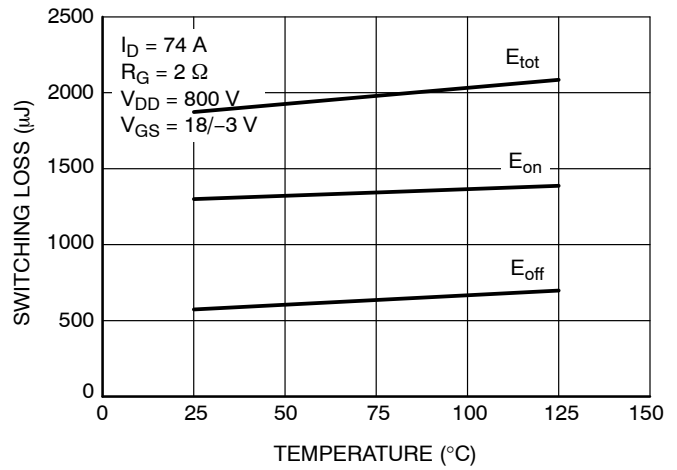


Figure 16. Switching Loss vs. Temperature

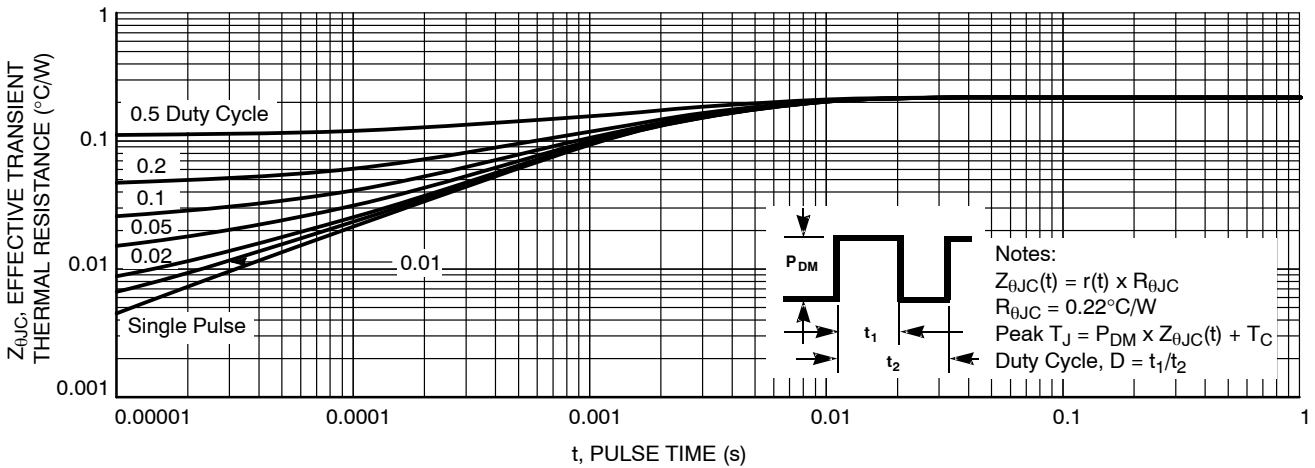


Figure 17. Junction-to-Case Transient Thermal Response

MECHANICAL CASE OUTLINE

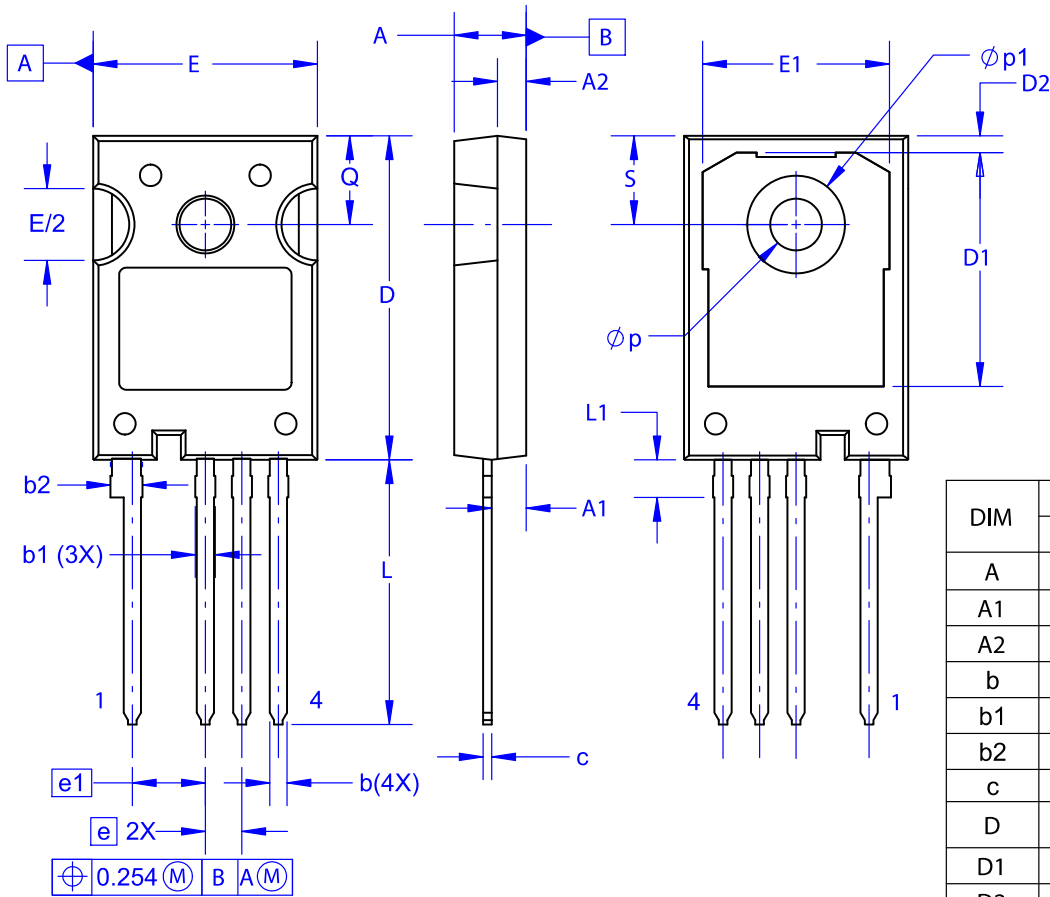
PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-4LD
CASE 340CJ
ISSUE A

DATE 16 SEP 2019



NOTES:

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.

DOCUMENT NUMBER:	98AON13852G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-247-4LD	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

 [View NTH4L014N120M3P on WIN SOURCE](#)

 [ON Semiconductor](#) Information

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management